

High Performance
32K×8 3.3V
CMOS SRAM



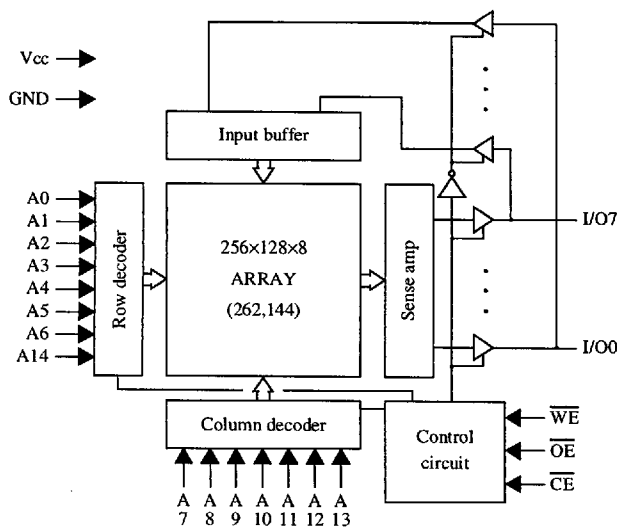
AS7C3256
AS7C3256L

Low voltage 32K×8 CMOS SRAM

Features

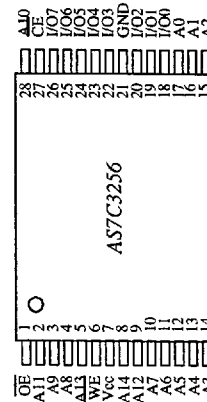
- Organization: 32,768 words × 8 bits
- Single $3.3 \pm 0.3V$ power supply
- 5V tolerant I/O specification
- High speed
 - 10/12/15/20 ns address access time
 - 3/3/4/5 ns output enable access time
- Very low power consumption
 - Active: 216 mW max, 10 ns cycle
 - Standby: 3.6 mW max, CMOS I/O
 - 1.1 mW max, CMOS I/O, L version
- 2.0V data retention
- Equal access and cycle times
- Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ inputs
- TTL-compatible, three-state I/O
- Ideal for cache, modem, portable computing
 - 75% power reduction during CPU idle mode
- 28-pin JEDEC standard packages
 - 300 mil PDIP and SOJ
 - 8×13.4 TSOP
- ESD protection ≥ 2000 volts
- Latch-up current ≥ 200 mA

Logic block diagram

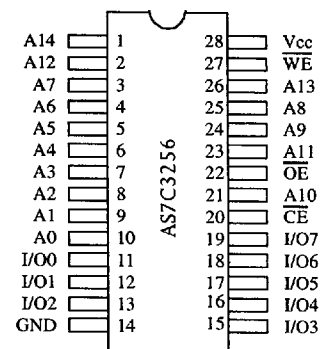


Pin arrangement

TSOP 8×13.4



DIP, SOJ



Selection guide

	7C3256-10	7C3256-12	7C3256-15	7C3256-20	Unit
Maximum address access time	10	12	15	20	ns
Maximum output enable access time	3	3	4	5	ns
Maximum operating current	60	55	50	45	mA
Maximum CMOS standby current	1.0	1.0	1.0	1.0	mA
	L	0.3	0.3	0.3	mA

Shaded areas contain advance information.

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Functional description

The AS7C3256 is a 3.3V high performance CMOS 262,144-bit Static Random-Access Memory (SRAM) organized as 32,768 words $\times$ 8 bits. It is designed for memory applications requiring fast data access at low voltage, including Pentium™, PowerPC™, and portable computing. Alliance's advanced circuit design and process techniques permit 3.3V operation without sacrificing performance or operating margins.

The device enters standby mode when $\overline{CE}$ is HIGH. CMOS standby mode consumes ≤ 3.6 mW (≤ 1.1 mW for the L version). Normal operation offers 75% power reduction after initial access, resulting in significant power savings during CPU idle, suspend, and stretch mode. Both versions of the AS7C3256 offer 2.0V data retention.

Equal address access and cycle times (t_{AA} , t_{RC} , t_{WC}) of 10/12/15/20 ns with output enable access times (t_{OE}) of 3/3/4/5 ns are ideal for high performance applications. The chip enable ($\overline{CE}$) input permits easy memory expansion with multiple-bank memory organizations.

A write cycle is accomplished by asserting chip enable ($\overline{CE}$) and write enable ($\overline{WE}$) LOW. Data on the input pins I/O0-I/O7 is written on the rising edge of $\overline{WE}$ (write cycle 1) or $\overline{CE}$ (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable ($\overline{OE}$) or write enable ($\overline{WE}$).

A read cycle is accomplished by asserting chip enable ($\overline{CE}$) and output enable ($\overline{OE}$) LOW, with write enable ($\overline{WE}$) HIGH. The chip drives I/O pins with the data word referenced by the input address. When chip enable or output enable is HIGH, or write enable is LOW, output drivers stay in high-impedance mode.

All chip inputs and outputs are TTL-compatible and 5V tolerant. Operation is from a single 3.3 ± 0.3 V supply. The AS7C3256 is packaged in high volume industry standard packages.

Absolute maximum ratings

Parameter	Symbol	Min	Max	Unit
Power supply voltage relative to GND	V_{CC}	-0.5	+4.6	V
Input voltage relative to GND	V_{IN}	-0.5	+6.0	V
Power dissipation	P_D	—	1.0	W
Storage temperature (plastic)	T_{stg}	-55	+150	°C
Temperature under bias	T_{bias}	-10	+85	°C
DC output current	I_{out}	—	20	mA

Stresses greater than those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Truth table

$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	Data	Mode
H	X	X	High Z	Standby (I_{SB} , I_{SB1})
L	H	H	High Z	Output disable
L	H	L	D_{out}	Read
L	L	X	D_{in}	Write

Key: X = Don't Care, L = LOW, H = HIGH

Recommended operating conditions

$(T_a = 0^\circ\text{C to } +70^\circ\text{C})$					
Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	3.0	3.3	3.6	V
	GND	0.0	0.0	0.0	V
Input voltage	V_{IH}	2.0	—	5.5	V
	V_{IL}	-0.5 [†]	—	0.8	V

[†] V_{IL} min = -2.0V for pulse width less than $t_{RC}/2$.

DC operating characteristics¹(V_{CC} = 3.3±0.3V, GND = 0V, T_a = 0°C to +70°C)

Parameter	Symbol	Test Conditions	-10		-12		-15		-20		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
Input leakage current	I _{LI}	V _{CC} = Max, V _{in} = GND to V _{CC}	—	1	—	1	—	1	—	1	μA
Output leakage current	I _{LO}	$\overline{CE} = V_{IH}$, V _{CC} = Max, V _{out} = GND to V _{CC}	—	1	—	1	—	1	—	1	μA
Operating power supply current	I _{CC}	$\overline{CE} = V_{IL}$, f = f _{max} , I _{out} = 0 mA	—	60	—	55	—	50	—	45	mA
Standby power supply current	I _{SB}	$\overline{CE} = V_{IH}$, f = f _{max}	—	25	—	20	—	20	—	15	mA
	I _{SB1}	$\overline{CE} \geq V_{CC}-0.2V$, V _{in} ≤ 0.2V or V _{in} ≥ V _{CC} -0.2V, f = 0	—	1.0	—	1.0	—	1.0	—	1.0	mA
		L	—	0.3	—	0.3	—	0.3	—	0.3	mA
Output voltage	V _{OL}	I _{OL} = 8 mA, V _{CC} = Min	—	0.4	—	0.4	—	0.4	—	0.4	V
	V _{OH}	I _{OH} = -4 mA, V _{CC} = Min	2.4	—	2.4	—	2.4	—	2.4	—	V

Shaded areas contain advance information.

Capacitance²(f = 1 MHz, T_a = Room Temperature, V_{CC} = 3.3V)

Parameter	Symbol	Signals	Test Conditions	Max	Unit
Input capacitance	C _{IN}	A, $\overline{CE}$, $\overline{WE}$, $\overline{OE}$	V _{in} = 0V	5	pF
I/O capacitance	C _{I/O}	I/O	V _{in} = V _{out} = 0V	7	pF

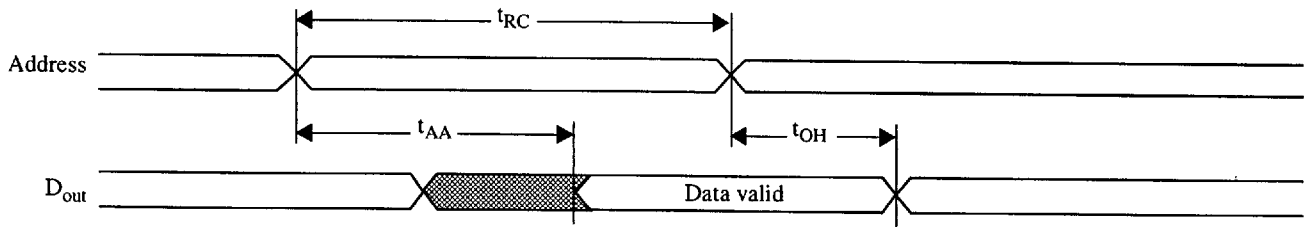
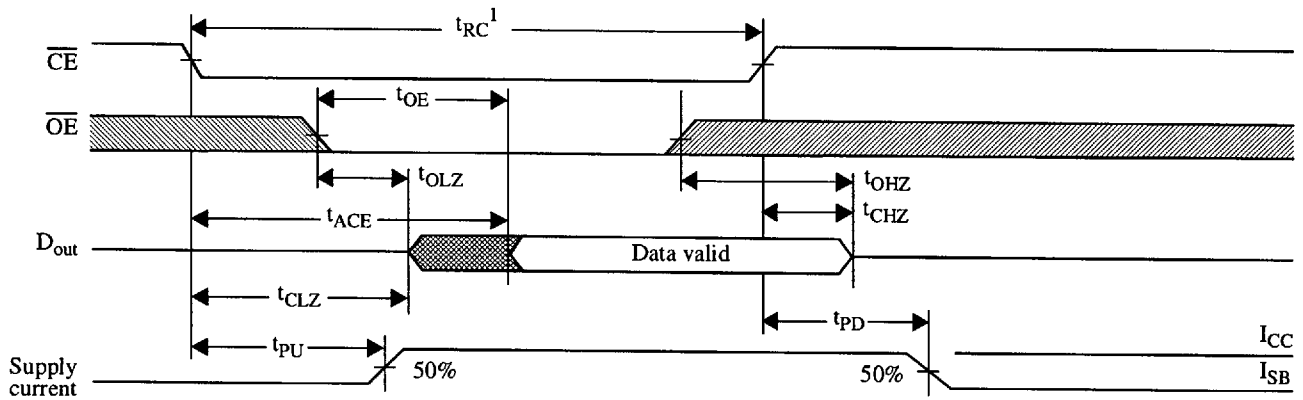
Read cycle^{3,9}(V_{CC} = 3.3±0.3V, GND = 0V, T_a = 0°C to +70°C)

Parameter	Symbol	-10		-12		-15		-20		Unit	Notes
		Min	Max	Min	Max	Min	Max	Min	Max		
Read cycle time	t _{RC}	10	—	12	—	15	—	20	—	ns	
Address access time	t _{AA}	—	10	—	12	—	15	—	20	ns	3
Chip enable ($\overline{CE}$) access time	t _{ACE}	—	10	—	12	—	15	—	20	ns	3
Output enable ($\overline{OE}$) access time	t _{OE}	—	3	—	3	—	4	—	5	ns	
Output hold from address change	t _{OH}	2	—	3	—	3	—	3	—	ns	5
$\overline{CE}$ LOW to output in Low Z	t _{CLZ}	3	—	3	—	3	—	3	—	ns	4, 5
$\overline{CE}$ HIGH to output in High Z	t _{CHZ}	—	3	—	3	—	4	—	5	ns	4, 5
$\overline{OE}$ LOW to output in Low Z	t _{OLZ}	0	—	0	—	0	—	0	—	ns	4, 5
$\overline{OE}$ HIGH to output in High Z	t _{OHZ}	—	3	—	3	—	4	—	5	ns	4, 5
Power up time	t _{PU}	0	—	0	—	0	—	0	—	ns	4, 5
Power down time	t _{PD}	—	10	—	12	—	15	—	20	ns	4, 5

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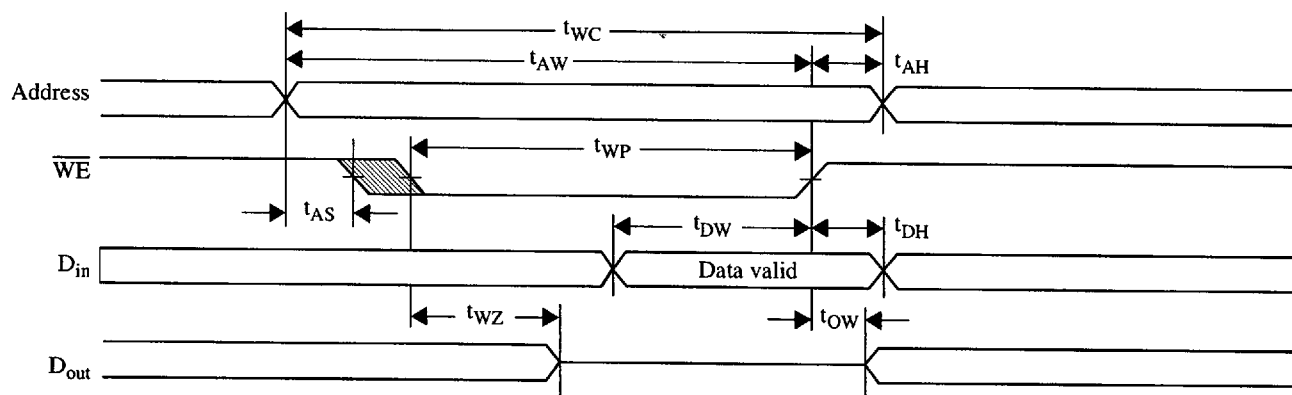
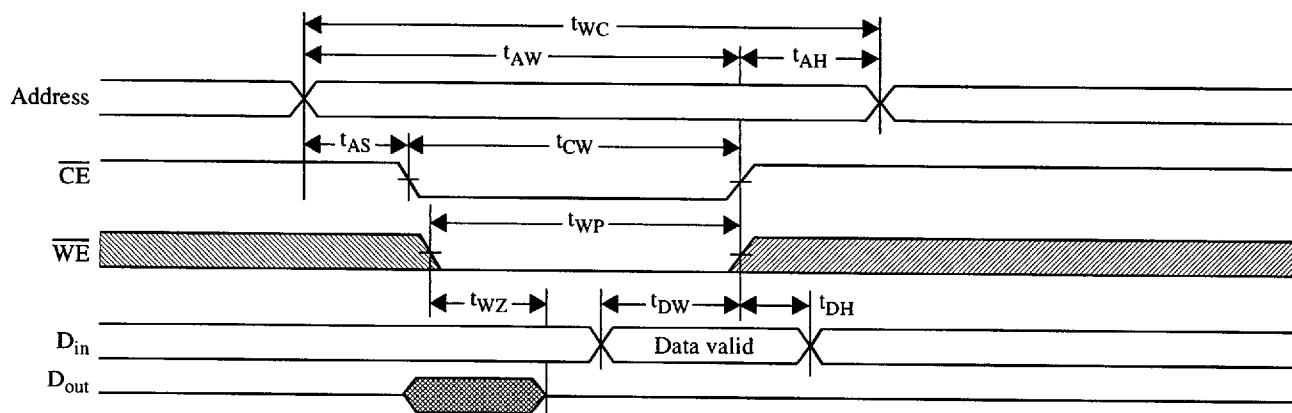
Read waveform 1^{3,6,7,9}

Address controlled

Read waveform 2^{3,6,8,9} $\overline{CE}$ controlledWrite cycle¹¹ $(V_{CC} = 3.3 \pm 0.3V, GND = 0V, T_a = 0 \text{ to } +70^\circ C)$

Parameter	Symbol	-10		-12		-15		-20		Unit	Notes
		Min	Max	Min	Max	Min	Max	Min	Max		
Write cycle time	t_{WC}	10	—	12	—	15	—	20	—	ns	
Chip enable to write end	t_{CW}	9	—	10	—	12	—	12	—	ns	
Address setup to write end	t_{AW}	9	—	10	—	12	—	12	—	ns	
Address setup time	t_{AS}	0	—	0	—	0	—	0	—	ns	
Write pulse width	t_{WP}	7	—	8	—	9	—	12	—	ns	
Address hold from end of write	t_{AH}	0	—	0	—	0	—	0	—	ns	
Data valid to write end	t_{DW}	6	—	6	—	8	—	10	—	ns	
Data hold time	t_{DH}	0	—	0	—	0	—	0	—	ns	4, 5
Write enable to output in High Z	t_{WZ}	—	5	—	5	—	5	—	5	ns	4, 5
Output active from write end	t_{OW}	3	—	3	—	3	—	3	—	ns	4, 5

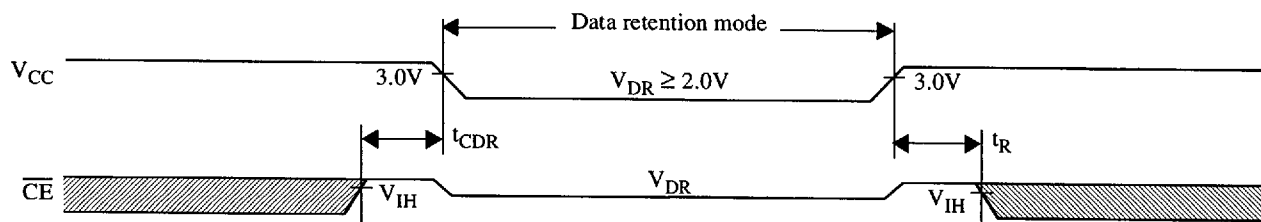
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Write waveform 1^{10,11} $\overline{WE}$ controlledWrite waveform 2^{10,11} $\overline{CE}$ controlled

Data retention characteristics

Parameter	Symbol	Test Conditions	Min	Max	Unit
V_{CC} for data retention	V_{DR}	$V_{CC} = 2.0V$	2.0	—	V
Data retention current	I_{CCDR}	$\overline{CE} \geq V_{CC} - 0.2V$	—	500	μA
Chip enable to data retention time	t_{CDR}	$V_{in} \geq V_{CC} - 0.2V$	0	—	ns
Operation recovery time	t_R	or $V_{in} \leq 0.2V$	t_{RC}	—	ns
Input leakage current	$ I_{LI} $		—	1	μA

Data retention waveform





AC test conditions

- Output load: see Figure B, except for t_{CLZ} and t_{CHZ} see Figure C.
- Input pulse level: GND to 3.0V. See Figure A.
- Input rise and fall times: 5 ns. See Figure A.
- Input and output timing reference levels: 1.5V.

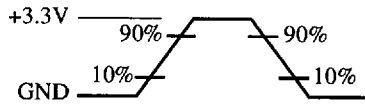


Figure A: Input waveform

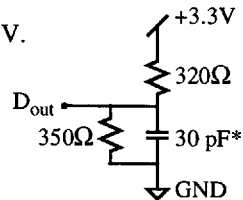
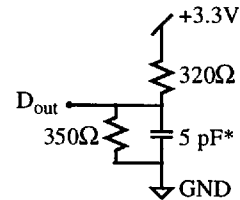
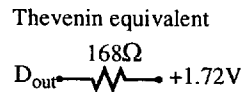


Figure B: Output load

Figure C: Output load for t_{CLZ} , t_{CHZ}

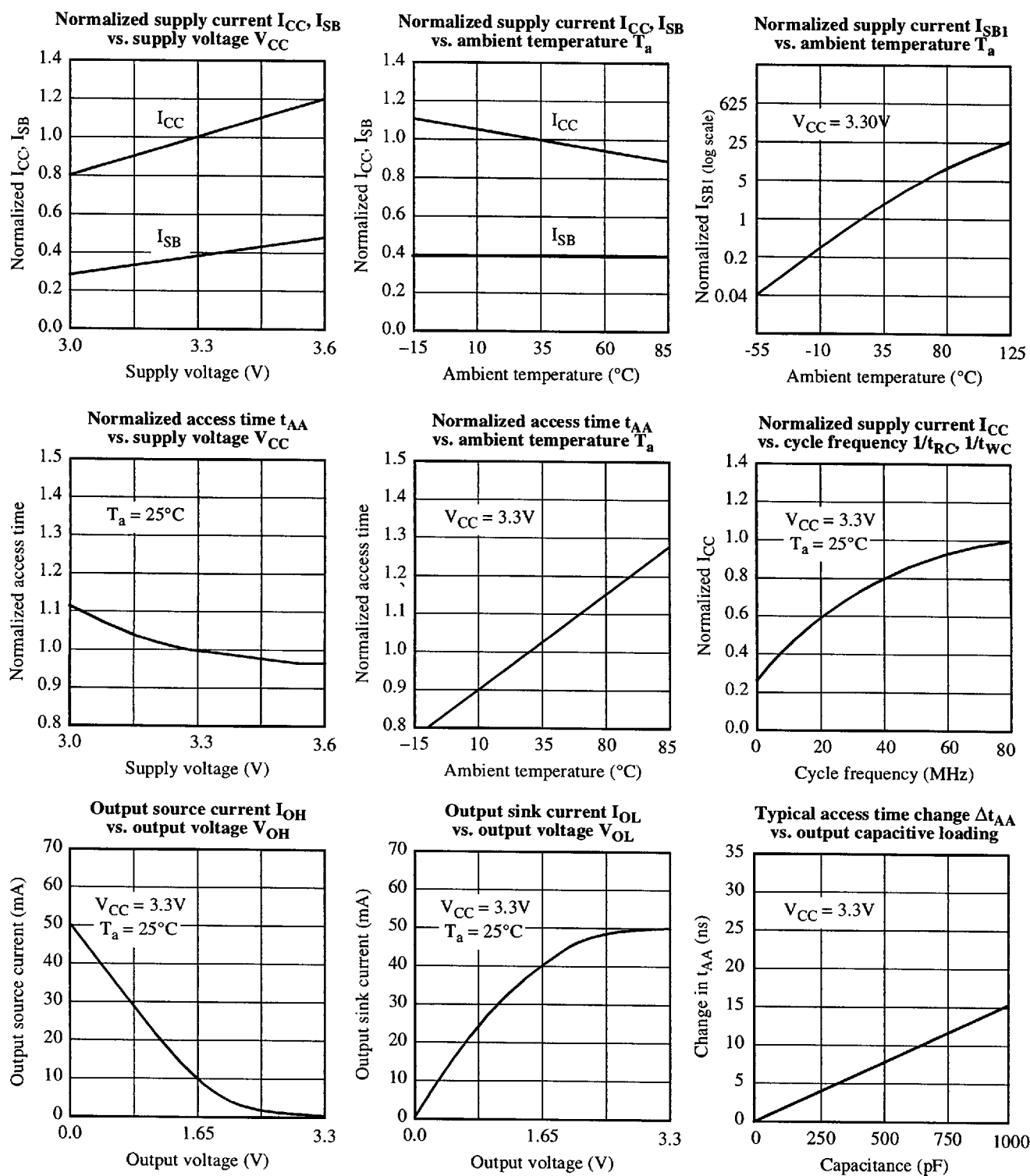
*including scope and jig capacitance

Notes

- 1 During V_{CC} power-up, a pull-up resistor to V_{CC} on $\overline{CE}$ is required to meet I_{SB} specification.
- 2 This parameter is sampled and not 100% tested.
- 3 For test conditions, see AC Test Conditions, Figures A, B, C.
- 4 t_{CLZ} and t_{CHZ} are specified with $CL = 5\text{ pF}$ as in Figure C. Transition is measured $\pm 500\text{ mV}$ from steady-state voltage.
- 5 This parameter is guaranteed but not tested.
- 6 $\overline{WE}$ is HIGH for read cycle.
- 7 $\overline{CE}$ and $\overline{OE}$ are LOW for read cycle.
- 8 Address valid prior to or coincident with $\overline{CE}$ transition LOW.
- 9 All read cycle timings are referenced from the last valid address to the first transitioning address.
- 10 $\overline{CE}$ or $\overline{WE}$ must be HIGH during address transitions.
- 11 All write cycle timings are referenced from the last valid address to the first transitioning address.



Typical DC and AC characteristics





Ordering information

Package / Access Time	10 ns	12 ns	15 ns	20 ns
Plastic DIP, 300 mil	AS7C3256-10PC AS7C3256L-10PC	AS7C3256-12PC AS7C3256L-12PC	AS7C3256-15PC AS7C3256L-15PC	AS7C3256-20PC AS7C3256L-20PC
Plastic SOJ, 300 mil	AS7C3256-10JC AS7C3256L-10JC	AS7C3256-12JC AS7C3256L-12JC	AS7C3256-15JC AS7C3256L-15JC	AS7C3256-20JC AS7C3256L-20JC
TSOP 8x13.4	AS7C3256-10TC AS7C3256L-10TC	AS7C3256-12TC AS7C3256L-12TC	AS7C3256-15TC AS7C3256L-15TC	AS7C3256-20TC AS7C3256L-20TC

Shaded areas contain advance information.

Part numbering system

AS7C	3	256	-XX	X	C
SRAM prefix	Blank = 5V supply 3 = 3.3V supply	Device number	Access Time	Package: P = PDIP 300 mil J = SOJ 300 mil T = TSOP 8x13.4	Commercial temperature range, 0°C to 70 °C
DOMESTIC REPS	ILLINOIS North: El-Mech (312) 94-9100 South: CenTech (314) 291-4230	NEBRASKA CenTech (816) 358-8100		PENNSYLVANIA East: Vantage Sales (610) 272-2125 West: Midwest Marketing (216) 381-8575	INTERNATIONAL AUSTRALIA Dunlop R&D Electronics +61-3-9558-0444 Brisbane: ACD +61-3-9762-7644
ALABAMA Concord Component	INDIANA CC Electro Sales (317) 921-5000	NEVADA North: Brooks Technical (415) 960-3880		RHODE ISLAND Kitchen & Kutchin (617) 229-2660	CANADA J-Squared Technologies
ARIZONA Competitive Technology (602) 265-9224	KANSAS CenTech (816) 358-8100	NEW HAMPSHIRE Kitchen & Kutchin (617) 229-2660		SOUTH CAROLINA Concord Component (919) 846-3441	CHINA (613) 592-9540
ARKANSAS Southern States Marketing (214) 238-7500	KENTUCKY CC Electro Sales (317) 921-5000	NEW JERSEY ERA Associates (800) 645-5500		SOUTH DAKOTA D. A. Case Associates (612) 831-6777	CHINA (905) 672-2030
CALIFORNIA North: Brooks Technical (415) 960-3880 LA Area: Competitive Tech. (714) 450-0170 San Diego: ATS (619) 634-1488	LOUISIANA Southern States Marketing	NEW MEXICO Competitive Tech. (602) 265-9224		TENNESSEE Concord Component (205) 772-8883	CHINA (613) 592-9540
COLORADO Technology Sales (303) 692-8835	MAINE Kitchen & Kutchin (617) 229-2660	NEW YORK NYC: ERA Associates (516) 543-0510		TEXAS Southern States Marketing	CHINA (905) 672-2030
CONNECTICUT Kitchen & Kutchin (203) 239-0212	MARYLAND Chesapeake Tech. (301) 236-0530	UPPER MERIDEN Tri-Tech (716) 385-6500		UTAH Charles Fields & Assoc. (801) 299-8228	CHINA (905) 672-2030
DELAWARE Vantage Sales (610) 272-2125	MASSACHUSETTS Kitchen & Kutchin (617) 229-2660	VERMONT Kitchen & Kutchin (617) 229-2660		VERMONT Kitchen & Kutchin (617) 229-2660	CHINA (905) 672-2030
FLORIDA Micro-Electronic Comp. Dunlop Branch (954) 426-8944 Orlando (407) 682-9602 Tampa (813) 393-5011	MICHIGAN Enco Group (810) 338-8600	VIRGINIA Chesapeake Tech. (301) 236-0530		WASHINGTON ES/Chase (206) 823-9535	CHINA (905) 672-2030
GEORGIA Concord Component (770) 416-9597	MINNESOTA D. A. Case Associates (612) 831-6777	WASHINGTON Midwest Marketing Assoc. (216) 381-8575		WEST VIRGINIA Chesapeake Tech. (301) 236-0530	CHINA (905) 672-2030
HAWAII Brooks Technical (415) 960-3880	MISSISSIPPI Concord Component (205) 772-8883	WISCONSIN D. A. Case Associates (612) 831-6777		WYOMING Technology Sales (303) 692-8835	CHINA (905) 672-2030
IDAHO ES/Chase (503) 684-8500	MONTANA ES/Chase (503) 684-8500	WYOMING Technology Sales (303) 692-8835			CHINA (905) 672-2030

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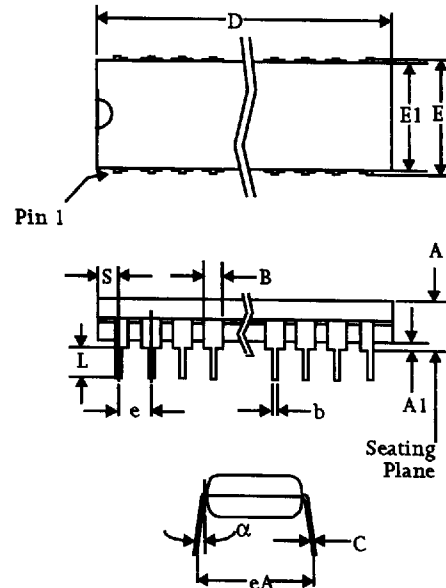
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Plastic dual in-line package (PDIP)

	20-pin 300 mil		28-pin 300 mil		32-pin 300 mil		32-pin 400 mil	
	Min	Max	Min	Max	Min	Max	Min	Max
A	-	0.175	-	0.175	-	0.180	-	0.200
A1	0.010	-	0.010	-	0.015	-	0.015	-
B	0.046	0.054	0.058	0.064	0.045	0.055	0.045	0.065
b	0.018	0.024	0.016	0.022	0.015	0.021	0.014	0.022
C	0.008	0.014	0.008	0.014	0.008	0.012	0.009	0.015
D	-	0.980	-	1.400	-	1.571	-	1.620
E	0.290	0.310	0.295	0.320	0.300	0.325	0.390	0.425
E1	0.263	0.293	0.278	0.298	0.280	0.295	0.340	0.390
e	0.100 BSC		0.100 BSC		0.100 BSC		0.100 BSC	
eA	0.310	0.350	0.330	0.370	0.330	0.370	0.430	0.470
L	0.110	0.130	0.120	0.140	0.110	0.142	0.118	0.162
α	0°	15°	0°	15°	0°	15°	0°	15°
S	-	0.040	-	0.055	-	0.043	-	0.065

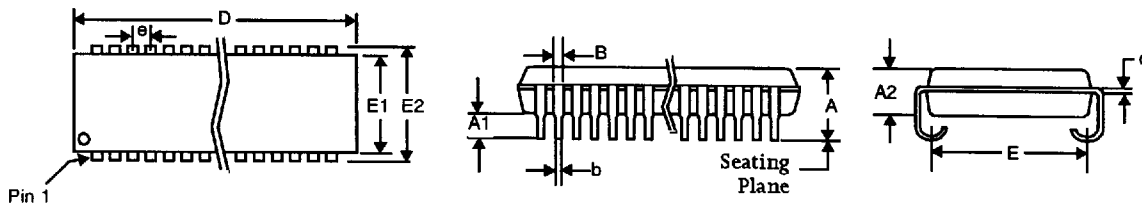
Dimensions in inches



Plastic small outline J-bend (SOJ)

	20/26-pin 300 mil		28-pin 300 mil		32-pin 300 mil		28-pin 400 mil		32-pin 400 mil		36-pin 400 mil		40-pin 400 mil		42-pin 400 mil		44-pin 400 mil	
	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
A	-	0.140	-	0.140	-	0.145	0.132	0.146	-	0.145	-	-	-	0.145	0.128	0.148	0.128	0.148
A1	0.020	-	0.025	-	0.025	-	0.062	-	0.025	-	-	-	0.025	-	0.025	-	0.025	-
A2	0.095	0.105	0.095	0.105	0.086	0.105	0.105	115	0.086	0.115	0.102	NOM	0.086	0.115	1.105	1.115	1.105	1.115
B	0.025	0.032	0.028	TYP	0.026	0.032	0.024	0.032	0.026	0.032	-	0.032	0.026	0.032	0.026	0.032	0.026	0.032
b	0.016	0.022	0.018	TYP	0.014	0.020	0.013	0.021	0.015	0.020	0.013	0.021	0.015	0.022	0.015	0.020	0.015	0.020
c	0.008	0.014	0.010	TYP	0.006	0.013	0.005	0.012	0.007	0.013	-	-	0.007	0.014	0.007	0.013	0.007	0.013
D	-	0.686	-	0.730	0.820	0.830	0.720	0.729	0.820	0.830	0.920	0.930	1.015	1.035	1.070	1.080	1.120	1.130
E	0.327	0.347	0.327	0.347	0.330	0.340	0.430	0.440	0.435	0.445	0.350	0.390	0.435	0.445	0.370	NOM	0.370	NOM
E1	0.295	0.305	0.295	0.305	0.292	0.305	0.395	0.405	0.395	0.405	0.400	NOM	0.395	0.405	0.395	0.405	0.395	0.405
E2	0.245	0.285	0.245	0.285	0.250	0.275	0.354	0.378	0.360	0.380	0.435	0.445	0.348	0.390	0.435	0.445	0.435	0.445
e	0.050 BSC		0.050 BSC		0.050 BSC		0.050 BSC		0.050 BSC		0.045	0.055	0.050 BSC		0.050 NOM		0.050 NOM	

Dimensions in inches



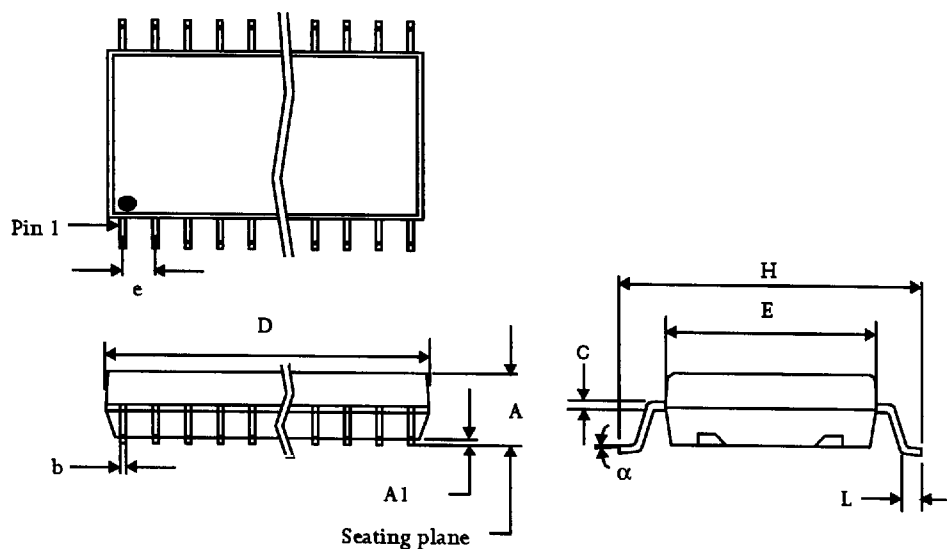
Package diagrams



Plastic small outline gull wing IC (SOIC)

28-pin 330 mil		
	Min	Max
A	-	0.112
A1	0.004	-
b	0.014	0.020
C	0.008	0.014
D	-	0.733
e	0.050 nominal	
E	0.326	0.336
H	0.453	0.477
L	0.028	0.044
α	0°	10°

Dimensions in inches



Thin small outline package (TSOP-I)

	28-pin 8×13.4		32-pin 8×20		40-pin 10×20	
	Min	Max	Min	Max	Min	Max
A	-	1.20	-	1.20	-	1.20
A1	0.05	0.15	0.05	0.15	0.05	0.15
A2	0.90	1.05	0.90	1.05	0.95	1.05
b	0.17	0.27	0.17	0.23	0.17	0.27
C	0.10	-	0.10	-	0.10	0.20
D	11.70	11.90	18.20	18.60	18.30	18.50
e	0.55 nominal		0.50 nominal		0.50 nominal	
E	8.0 nominal		7.80	8.20	9.90	10.10
Hd	13.20	13.60	19.80	20.20	19.80	20.20
L	0.30	0.70	0.40	0.60	0.50	0.70
α	0°	5°	1°	5°	0°	5°

Dimensions in millimeters

